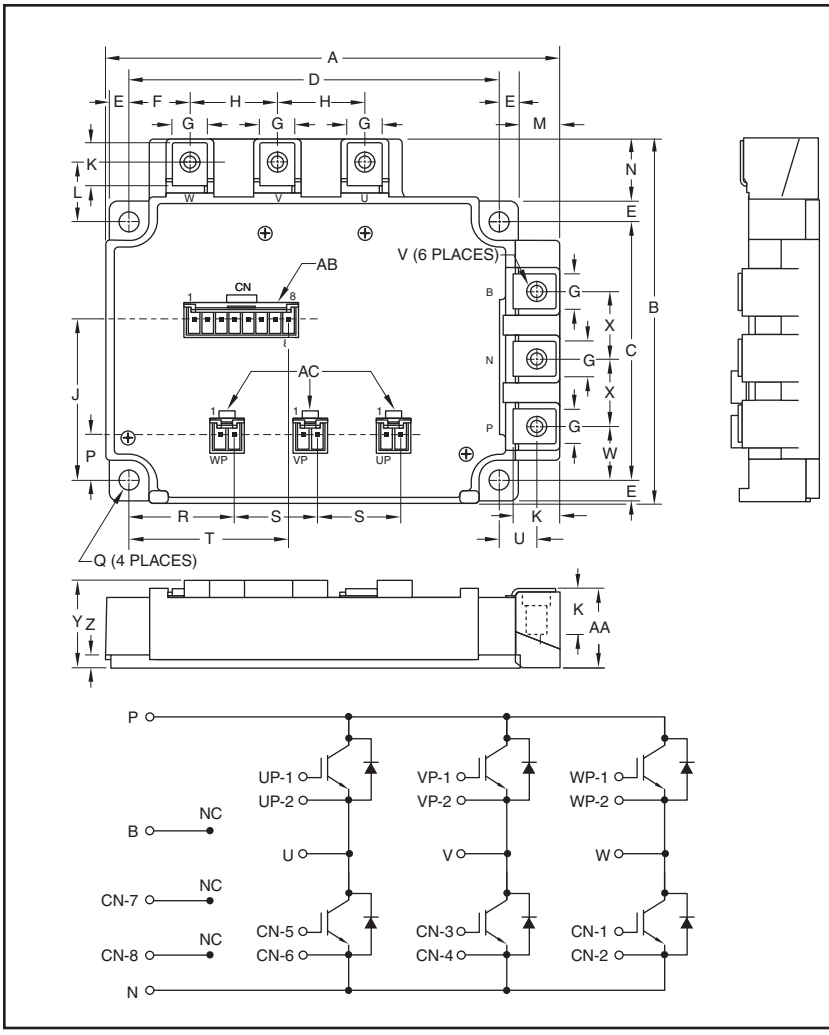
Powerex, Inc., 173 Pavilion Lane, Youngwood, Pennsylvania 15697 (724) 925-7272
www.pwrx.com

CM150TL-24NF

Six IGBTMOD™ NF-Series Module
150 Amperes/1200 Volts



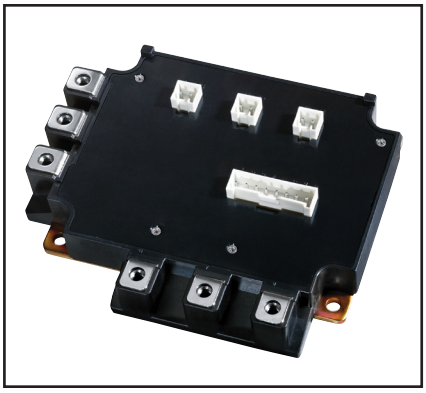
Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.32	135.0
B	4.33	110.0
C	3.07±0.02	78.0±0.5
D	4.33±0.02	110.0±0.5
E	0.24	6.05
F	0.69	17.5
G	0.41	10.5
H	1.02	26.0
J	1.92	48.75
K	0.51	13.0
L	0.71	18.0
M	0.46	11.7

Dimensions	Inches	Millimeters
N	0.74	18.7
P	0.54	13.75
Q	0.22	5.5 Dia.
R	1.20	30.5
S	0.98	25.0
T	1.82	46.3
U	0.43	11.0
V	M5	M5
W	0.65	16.5
X	0.78	20.0
Y	1.04	26.5
Z	0.16	4.0
AA	0.95+0.04/-0.0	24.1+1.0/-0.0

Housing Types (J.S.T. Mfg. Co. Ltd.)

AB – B8P-VH-FB-B
AC – B2P-VH-FB-B



Description:
Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of six IGBT Transistors in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:
- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:
- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Photovoltaic/Fuel Cell

Ordering Information:
Example: Select the complete module number you desire from the table below -i.e. CM150TL-24NF is a 1200V (V_{CES}), 150 Ampere Six-IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	150	24

CM150TL-24NF
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Absolute Maximum Ratings, T_j = 25°C unless otherwise specified

Characteristics	Symbol	CM150TL-24NF	Units
Power Device Junction Temperature	T_j	-40 to 150	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Collector-Emitter Voltage (G-E Short)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E Short)	V_{GES}	±20	Volts
Collector Current (DC, T_C = 76°C)*4	I_C	150	Amperes
Peak Collector Current (Pulse, Repetitive)*2	I_{CM}	300	Amperes
Emitter Current (DC, T_C = 25°C)*4	I_E*1	150	Amperes
Peak Emitter Current (Pulse, Repetitive)*2	I_{EM}*1	300	Amperes
Maximum Collector Dissipation (T_C = 25°C)*2,*4	P_C	890	Watts
Mounting Torque, M5 Mounting Screws	—	31	in-lb
Mounting Torque, M5 Main Terminal Screws	—	31	in-lb
Module Weight (Typical)	—	750	Grams
Isolation Voltage, AC 1 minute, 60Hz Sinusoidal	V_{ISO}	2500	Volts

Electrical and Mechanical Characteristics, T_j = 25°C unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector Cutoff Current		I_{CES}	$V_{CE} = V_{CES}$, V_{GE} = 0V	—	—	1.0	mA
Gate-Emitter Threshold Voltage		$V_{GE(th)}$	I_C = 15mA, V_{CE} = 10V	6	7	8	Volts
Gate Leakage Current		I_{GES}	$\pm V_{GE} = V_{GES}$, V_{CE} = 0V	—	—	0.5	µA
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C = 150A, V_{GE} = 15V, T_j = 25°C*3	—	2.1	3.0	Volts
			I_C = 150A, V_{GE} = 15V, T_j = 125°C*3	—	2.4	—	Volts
Forward Transfer Admittance		$\lvert y_{fs} \rvert$	I_C = 150A, V_{CE} = 10V*3	45	—	—	sec
Input Capacitance		C_{ies}	V_{CE} = 10V, V_{GE} = 0V	—	—	23.0	nf
Output Capacitance		C_{oes}		—	—	2.0	nf
Reverse Transfer Capacitance		C_{res}		—	—	0.45	nf
Total Gate Charge		Q_G	V_{CC} = 600V, I_C = 150A, V_{GE} = 15V	—	675	—	nC
Inductive	Turn-on Delay Time	$t_{d(on)}$	V_{CC} = 600V, I_C = 150A, $V_{GE1} = V_{GE2}$ = 15V, R_G = 2.1Ω, I_E = 150A, Inductive Load Switching Operation	—	—	130	ns
Load	Turn-on Rise Time	t_r		—	—	70	ns
Switch	Turn-off Delay Time	$t_{d(off)}$		—	—	400	ns
Time	Turn-off Fall Time	t_f		—	—	350	ns
Reverse Recovery Time*1		t_{rr}		—	—	150	ns
Reverse Recovery Charge*1		Qrr		—	5.8	—	µC
Emitter-Collector Voltage*1		V_{EC}	I_E = 150A, V_{GE} = 0V	—	—	3.8	Volts

*1 I_E, I_{EM}, V_{EC}, t_{rr}, and Q_{rr} represent characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).
*2 Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.
*3 Pulse width and repetition rate should be such as to cause negligible temperature rise.
*4 T_C measured point is just under the chips.

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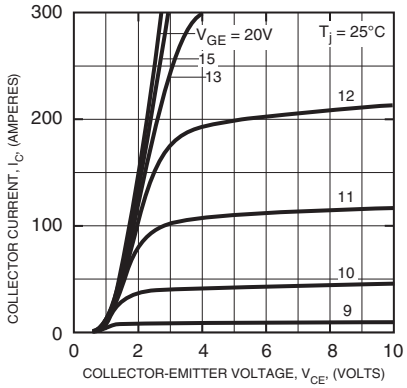
Thermal and Mechanical Characteristics, T_j = 25°C unless otherwise specified

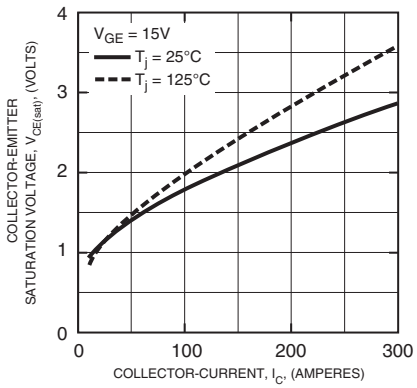
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case*	$R_{th(j-c)}Q$	Per IGBT 1/6 Module*4	—	—	0.14	°C/W
Thermal Resistance, Junction to Case*	$R_{th(j-c)}D$	Per FWDi 1/6 Module*4	—	—	0.23	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/6 Module, Thermal Grease Applied*4	—	0.051	—	°C/W
External Gate Resistance	R_G		2.1	—	31	Ω

*4 T_C, T_f measured point is just under the chips.

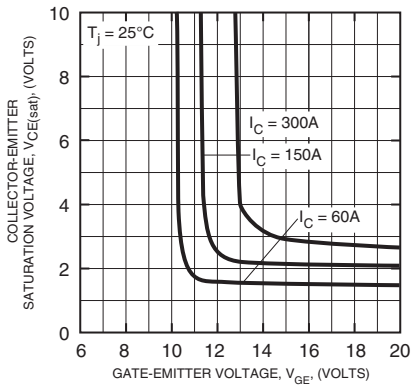
OUTPUT CHARACTERISTICS (TYPICAL)



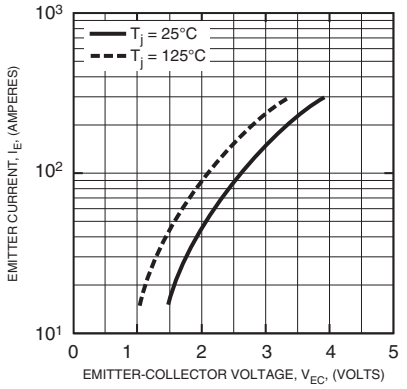
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



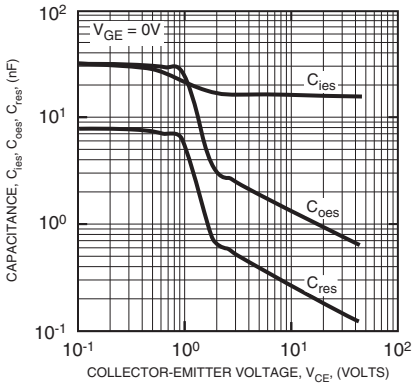
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



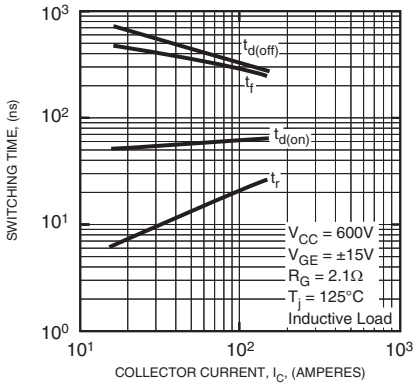
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



CAPACITANCE VS. V_{CE} (TYPICAL)



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



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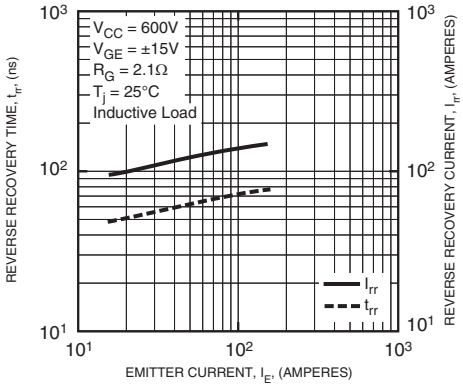
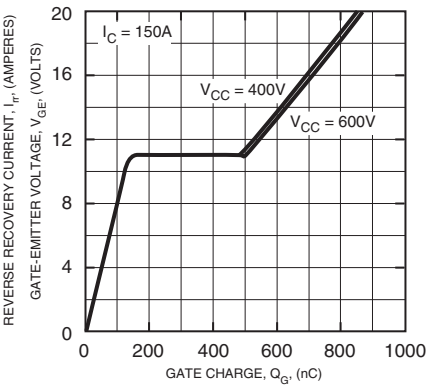
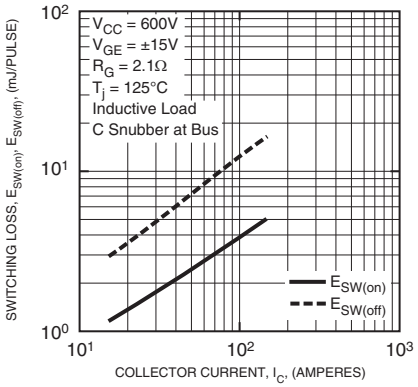
REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



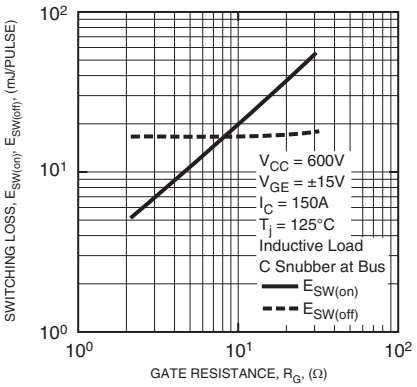
GATE CHARGE VS. V_{GE}



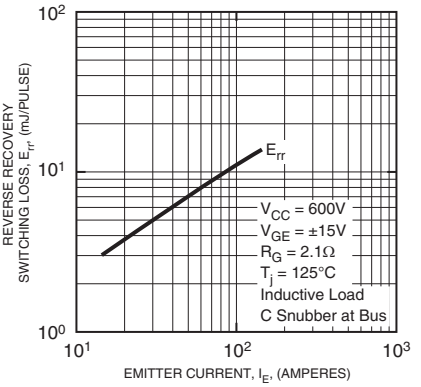
SWITCHING LOSS VS. COLLECTOR CURRENT (TYPICAL)



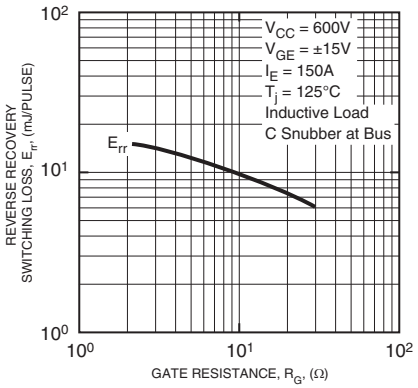
SWITCHING LOSS VS. GATE RESISTANCE (TYPICAL)



REVERSE RECOVERY SWITCHING LOSS VS. EMITTER CURRENT (TYPICAL)



REVERSE RECOVERY SWITCHING LOSS VS. GATE RESISTANCE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT & FWDi)